imall

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The Future of Analog IC Technology

DESCRIPTION

The MP1921A is a high-frequency, 100V, half bridge, N-channel power MOSFET driver. Its low side and high side driver channels are independently controlled and matched with a time delay of less than 5ns. Under-voltage lockout on both high side and low side supplies force their outputs low in case of insufficient supply. The integrated bootstrap diode reduces external component count.

FEATURES

- Drives N-Channel MOSFET Half Bridge
- 120V V_{BST} Voltage Range
- On-Chip Bootstrap Diode
- Typical 16ns Propagation Delay Time
- Less Than 5ns Gate Drive Matching
- Drives 1nf Load with 12ns/9ns Rise/Fall Times with 12V VDD
- TTL Compatible Input
- Less Than 150μA Quiescent Current
- UVLO for Both High Side and Low Side
- In SOIC8E, SOIC-8, 3×3mm QFN8, 3×3mm QFN9 and 4x4mm QFN10 Packages

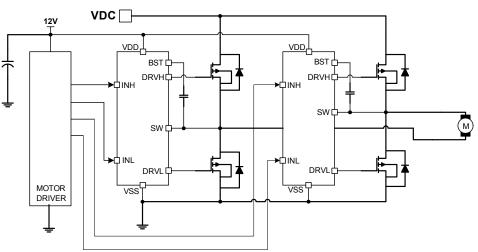
APPLICATIONS

- Telecom Half Bridge Power Supplies
- Avionics DC-DC Converters
- Two-Switch Forward Converters
- Active Clamp Forward Converters
- DC Motor Drivers

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TYPICAL APPLICATION



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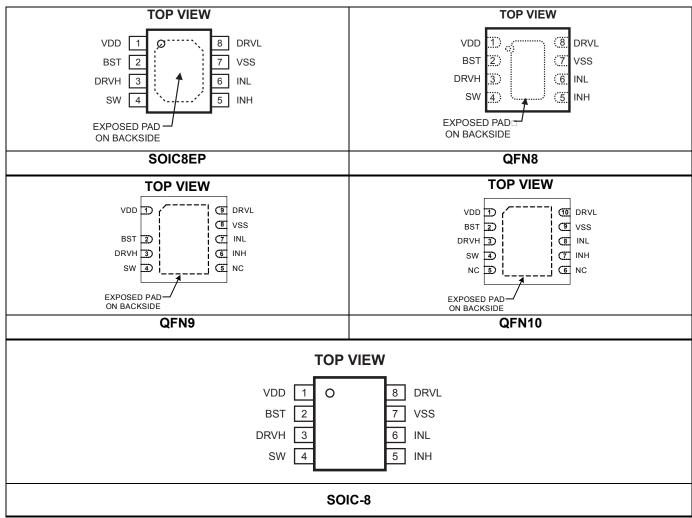


ORDERING INFORMATION

Part Number	Package	Top Marking
MP1921HN-A*	SOIC8E	MP1921-A
MP1921HQ-A	QFN8 (3x3mm)	AHA
MP1921HQE-A	QFN9 (3x3mm)	AHL
MP1921HR-A	QFN10 (4x4mm)	MP1921 A
MP1921HS-A	SOIC-8	MP1921-A

* For Tape & Reel, add suffix –Z (e.g. MP1921HN–A–Z);

For RoHS compliant packaging, add suffix –LF (e.g. MP1921HN–A–LF–Z)



PACKAGE REFERENCE



ABSOLUTE MAXIMUM RATINGS (1)

Recommended Operating Conditions ⁽³⁾						
Supply Voltage (V _{DD})	9.0V to 18V					
SW Voltage (V _{SW})	1.0V to +100V					
SW slew rate	<50V/nsec					
Operating Junction Temp. (T _J)40°C to +125°C					

Thermal Resistance ⁽⁴⁾	$\boldsymbol{\theta}_{JA}$	$\boldsymbol{\theta}_{JC}$
SOIC8E	. 48	. 10 °C/W
QFN8 (3x3mm)	. 50	. 12 °C/W
QFN9 (3x3mm)	. 50	. 12 °C/W
QFN10 (4x4mm)	. 47	7 °C/W
SOIC-8	. 96	. 45 °C/W

Notes:

1) Exceeding these ratings may damage the device.

²⁾ The maximum allowable power dissipation is a function of the maximum junction temperature $T_J(MAX)$, the junction-toambient thermal resistance θ_{JA} , and the ambient temperature T_A . The maximum allowable continuous power dissipation at any ambient temperature is calculated by $P_D(MAX)=(T_J(MAX)-T_A)/\theta_{JA}$. Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.

³⁾ The device is not guaranteed to function outside of its operating conditions.

⁴⁾ Measured on JESD51-7, 4-layer PCB.



ELECTRICAL CHARACTERISTICS

$V_{DD} = V_{BST}-V_{SW}=12V$, $V_{SS}=V_{SW}=0V$, No load at DRVH and DRVL, $T_A=25^{\circ}C$, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Supply Currents						
VDD quiescent current		INL=INH=0		100	150	μA
VDD operating current	I _{DDO}	f _{sw} =500kHz		2.8	3.5	mA
Floating driver quiescent current	I _{BSTQ}	INL=INH=0		60	90	μA
Floating driver operating current	I _{BSTO}	f _{sw} =500kHz		2.1	3	mA
Leakage Current	I _{LK}	BST=SW=100V		0.05	1	μA
Inputs						
INL/INH High				2	2.4	V
INL/INH Low			1	1.4		V
INL/INH internal pull-down resistance	R _{IN}			185		kΩ
Under Voltage Protection						
VDD rising threshold	V_{DDR}		7.7	8.1	8.5	V
VDD hysteresis	V _{DDH}			0.5		V
(BST-SW) rising threshold	V _{BSTR}		6.7	7.1	7.5	V
(BST-SW) hysteresis	V _{BSTH}			0.55		V
Bootstrap Diode	Donn					
Bootstrap diode VF @ 100uA	V _{F1}			0.5		V
Bootstrap diode VF @ 100mA	V _{F2}			0.9		V
Bootstrap diode dynamic R	R _D	@ 100mA		2.5		Ω
Low Side Gate Driver						
Low level output voltage	V _{OLL}	I ₀ =100mA		0.15	0.22	V
High level output voltage to rail	V _{OHL}	I _o =-100mA		0.45	0.6	V
Peak pull-up current	I _{OHL}	V _{DRVL} =0V, V _{DD} =12V		1.5		А
Peak puil-up cuitent		V _{DRVL} =0V, V _{DD} =16V		2.5		А
Peak pull-down current	I _{OLL}	V _{DRVL} =V _{DD} =12V		2.5		А
Peak puil-down current		V _{DRVL} =V _{DD} =16V		3.5		Α
Floating Gate Driver						
Low level output voltage	V_{OLH}	I _o =100mA		0.15	0.22	V
High level output voltage to rail	V _{OHH}	I _o =-100mA		0.45	0.6	V
	I _{ОНН}	$V_{DRVH}=0V, V_{DD}=12V$		1.5		Α
Peak pull-up current		V _{DRVH} =0V, V _{DD} =16V		2.5		Α
Peak pull-down current	.	V _{DRVH} =V _{DD} =12V		2.5		Α
r eak puil-uown current	I _{OLH}	V _{DRVH} =V _{DD} =16V		3.5		Α



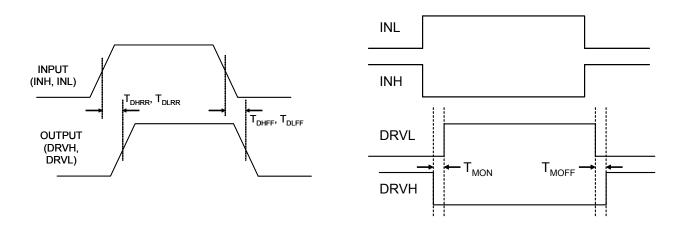
ELECTRICAL CHARACTERISTICS (continued)

$V_{DD} = V_{BST}-V_{SW}=12V$, $V_{SS}=V_{SW}=0V$, No load at DRVH and DRVL, $T_A=25^{\circ}C$, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Switching Spec Low Side Gate Driver						
Turn-off propagation delay INL falling to DRVL falling	T_{DLFF}			16		ns
Turn-on propagation delay INL rising to DRVL rising	T _{DLRR}			16		
DRVL rise time		C _L =1nF		12		ns
DRVL fall time		C _L =1nF		9		ns
Switching Spec Floating Gate	e Driver					
Turn-off propagation delay INL falling to DRVH falling	T_{DHFF}			16		ns
Turn-on propagation delay INL rising to DRVH rising	T _{DHRR}			16		ns
DRVH rise time		C _L =1nF		12		ns
DRVH fall time		C _L =1nF		9		ns
Switching Spec Matching						
Floating driver turn-off to low side drive turn-on	T _{MON}			1	5	ns
Low side driver turn-off to floating driver turn-on	T _{MOFF}			1	5	ns
Minimum input pulse width that changes the output	T_{PW}				50 ⁽⁵⁾	ns
Bootstrap diode turn-on or turn- off time	T _{BS}			10 ⁽⁵⁾		ns

Note:

5) Guaranteed by design.

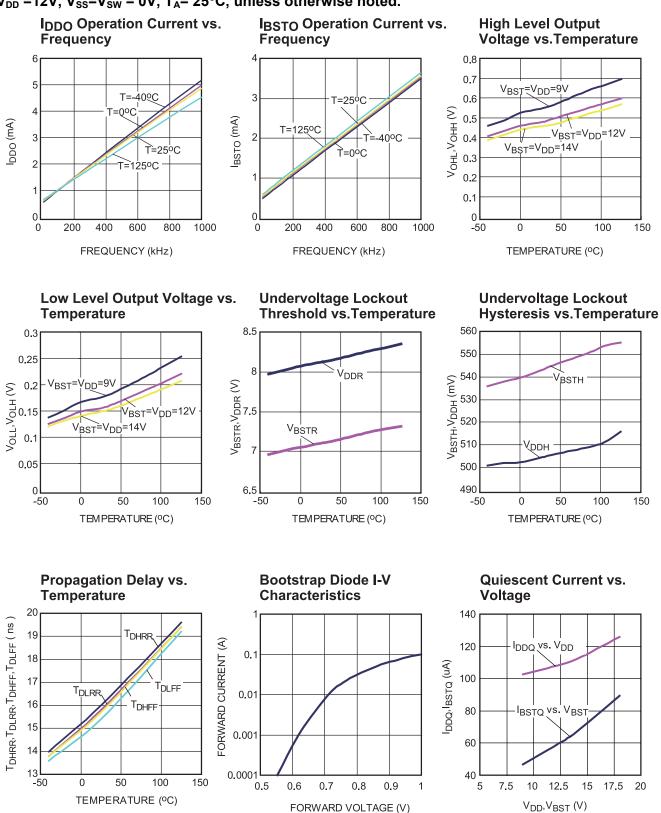








 V_{DD} =12V, V_{SS} = V_{SW} = 0V, T_A = 25°C, unless otherwise noted.

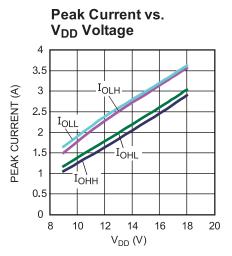


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TYPICAL PERFORMANCE CHARACTERISTICS (continued)

 V_{DD} =12V, V_{SS} = V_{SW} = 0V, T_A = 25°C, unless otherwise noted.



Turn-on Propagation Delay

16.0ns

INH:

INL

DRVL

DRVH

10V/div.

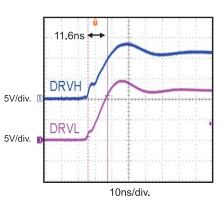
10V/div.

10V/div

Gate Drive Matching TMOFF

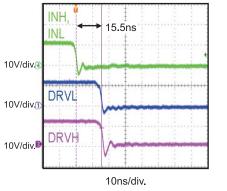
INH - 0.96ns 10V/div. 1 10V/div. 2 DRVH 10V/div. DRVL 10V/div. 4ns/div.

Drive Rise Time (1nF Load)



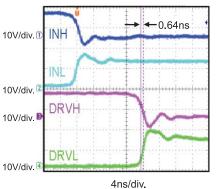


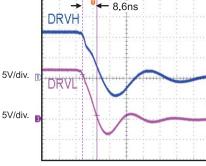
10ns/div.





Drive Fall Time (1nF Load)





-





PIN FUNCTIONS

SOIC8EP, SOIC-8, QFN8(3x3mm)	QFN9 (3x3mm)	QFN10 (4x4mm)	Name	Description
1	1	1	VDD	Supply input. This pin supplies power to all the internal circuitry. A decoupling capacitor to ground must be placed close to this pin to ensure stable and clean supply.
2	2	2	BST	Bootstrap. This is the positive power supply for the internal floating high-side MOSFET driver. Connect a bypass capacitor between this pin and SW pin.
3	3	3	DRVH	Floating driver output.
4	4	4	SW	Switching node.
	5	5,6	NC	No connection.
5	6	7	INH	Control signal input for the floating driver.
6	7	8	INL	Control signal input for the low side driver.
7	8	9	VSS, Exposed Pad	Chip ground. Connect exposed pad to VSS for proper thermal operation.
8	9	10	DRVL	Low side driver output.



BLOCK DIAGRAM

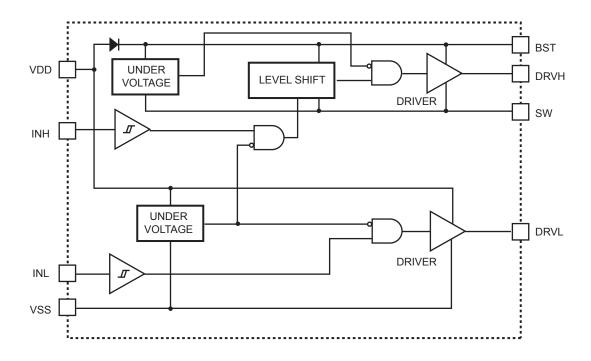
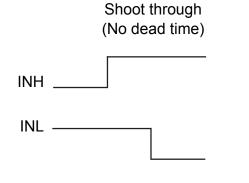


Figure 2—Function Block Diagram

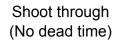


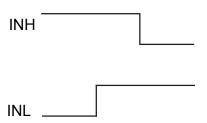
APPLICATION

The input signals of INH and INL can be controlled independently. If both INH and INL are controlling HSFET and LSFET of the same bridge, then users must avoid shoot through by

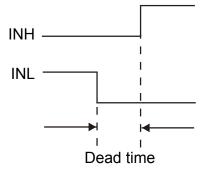


setting sufficient dead time between INH and INL low, and vice versa. See below figure. Dead time is defined as the time internal between INH low and INL low.

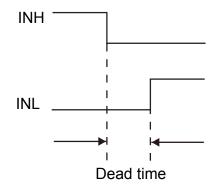




No Shoot through



No Shoot through





REFERENCE DESIGN CIRCUITS

Half Bridge Converter

In half-bridge converter topology, the MOSFETs are driven alternately with some dead time. Therefore, INH and INL are driven with

alternating signals from the PWM controller. The input voltage can be up to 100V in this application.

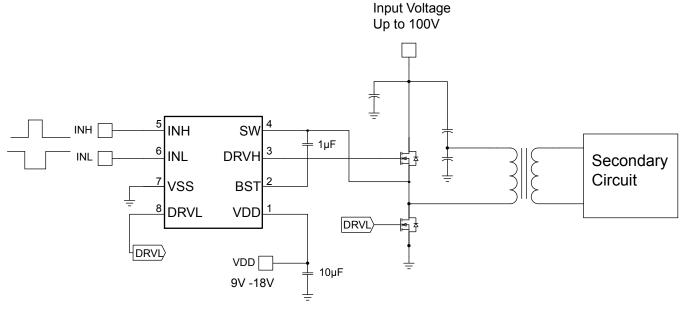
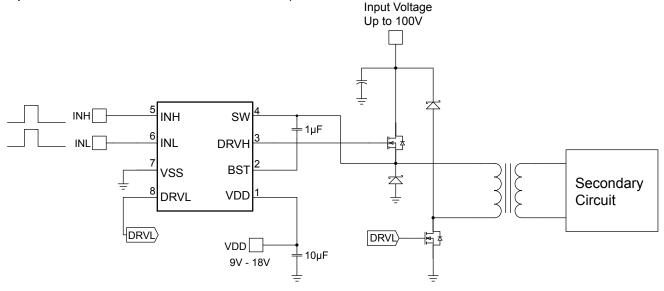


Figure 3 – Half Bridge Converter

Two-Switch Forward Converter

In two-switch forward converter topology, both MOSFETs are turned on and off together. The input signal (INH and INL) comes from the PWM controller, which senses the output voltage (and output current if current-mode control is used).

The Schottky diodes clamp the reverse swing of the power transformer and must be rated at the input voltage. The input voltage can be up to 100V in this circuit.







Active-Clamp Forward Converter

In active-clamp forward converter topology, the MOSFETs are driven alternately. The high-side MOSFET, along with capacitor C_{reset} , is used to reset the power transformer in a lossless manner.

This topology lends itself well to run at duty cycles exceeding 50%. For these reasons, the input voltage may not be able to run at 100V for this application.

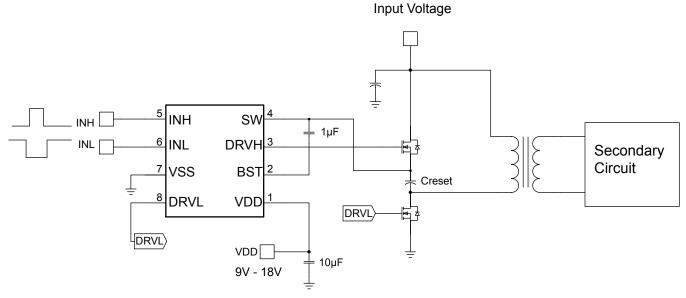
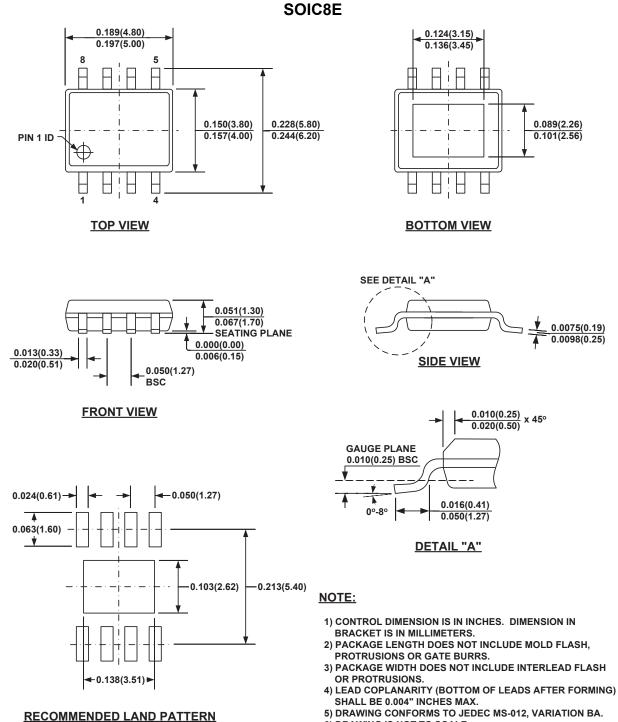


Figure 5 – Active-Clamp Forward Converter



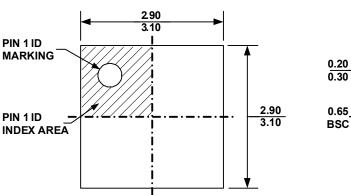
PACKAGE INFORMATION



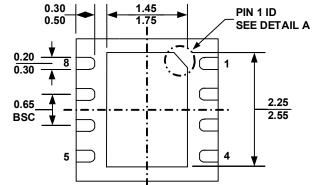
5) DRAWING CONFORMS TO JEDEC MS-012, VARIATION BA.



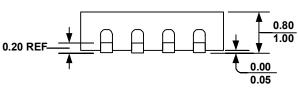
QFN8 (3×3mm)



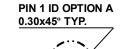
TOP VIEW

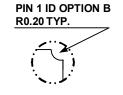


BOTTOM VIEW

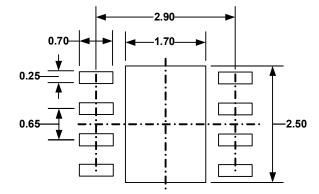


SIDE VIEW





DETAIL A



RECOMMENDED LAND PATTERN

NOTE:

1) ALL DIMENSIONS ARE IN MILLIMETERS

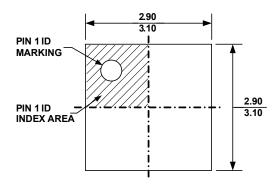
2) EXPOSED PADDLE SIZE DOES NOT INCLUDE MOLD FLASH

3) LEAD COPLANARITY SHALL BED.10 MILLIMETER MAX 4) DRAWING CONFORMS TO JEDEC MO229, VARIATION VEEC-2.

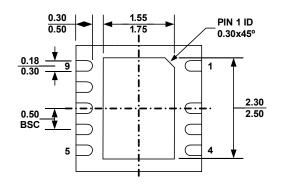
4) DRAWING CONFORMS TO JEDEC M 5) DRAWING IS NOT TO SCALE



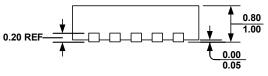
QFN9 (3×3mm)



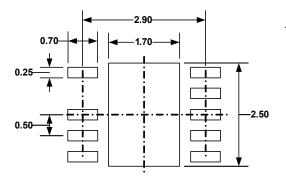




BOTTOM VIEW







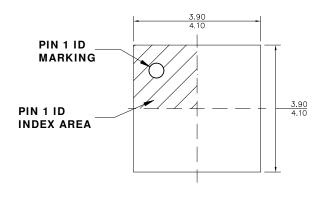
RECOMMENDED LAND PATTERN

NOTE:

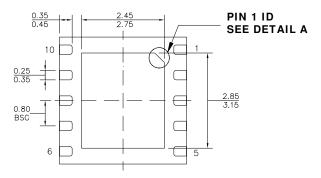
1) ALL DIMENSIONS ARE IN MILLIMETERS 2) EXPOSED PADDLE SIZE DOES NOT INCLUDE MOLD FLASH 3) LEAD COPLANARITY SHALL BE0.10 MILLIMETER MAX 4) DRAWING CONFORMS TO JEDEC MO.229, VARIATION VEED-5. 5) DRAWING IS NOT TO SCALE



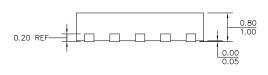
QFN10 (4×4mm)



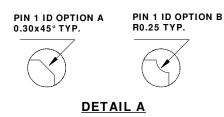
TOP VIEW

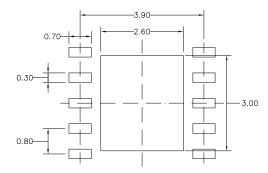


BOTTOM VIEW



SIDE VIEW





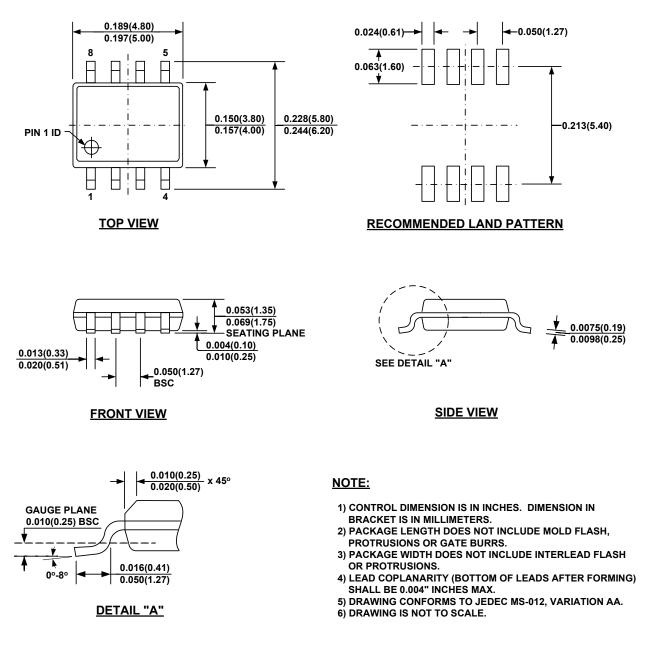
RECOMMENDED LAND PATTERN

NOTE:

 ALL DIMENSIONS ARE IN MILLIMETERS.
EXPOSED PADDLE SIZE DOES NOT INCLUDE MOLD FLASH.
LEAD COPLANARITY SHALL BE 0.10 MILLIMETERS MAX.
JEDEC REFERENCE IS MO-220.
DRAWING IS NOT TO SCALE.







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